

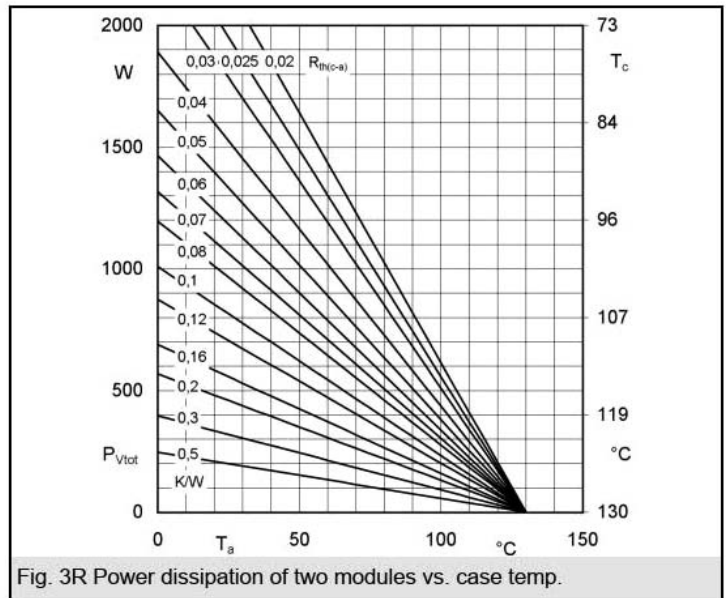
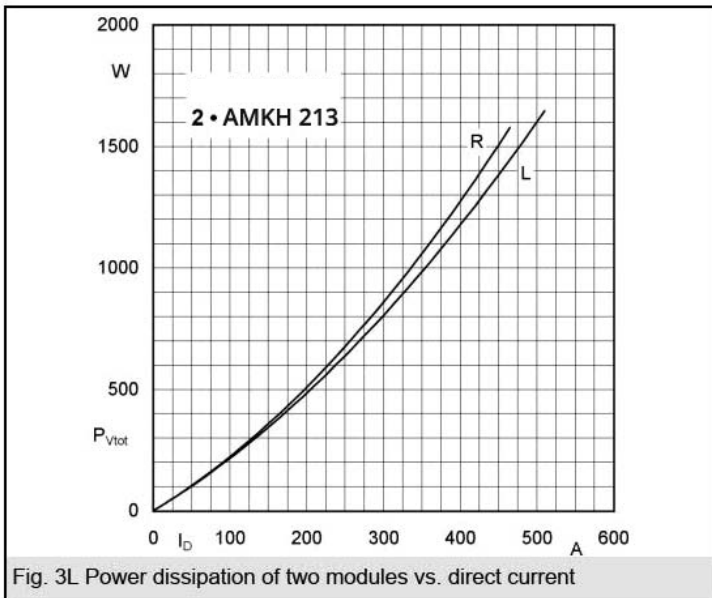
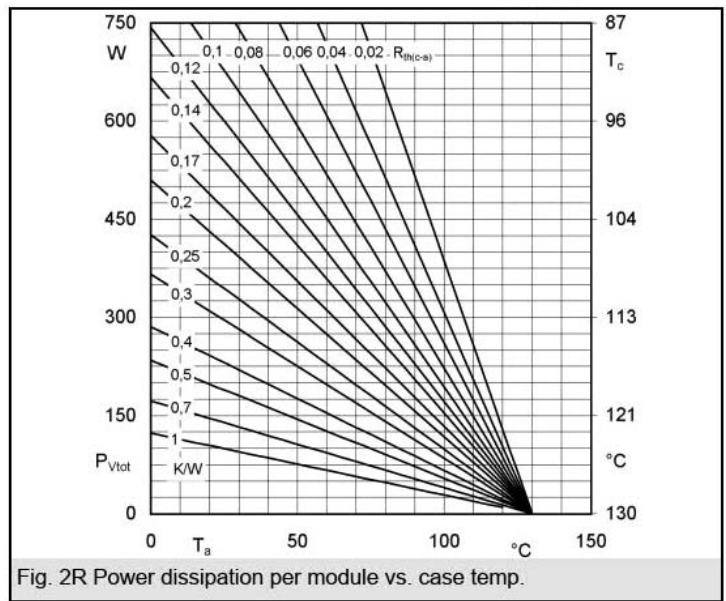
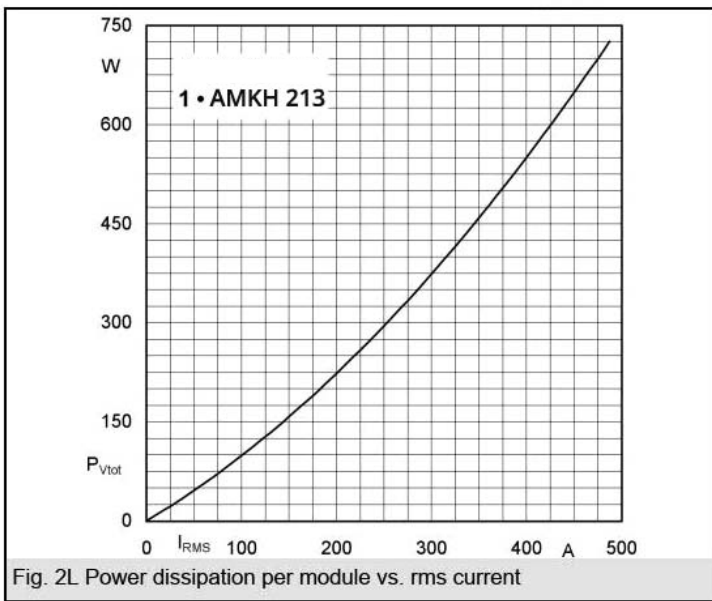
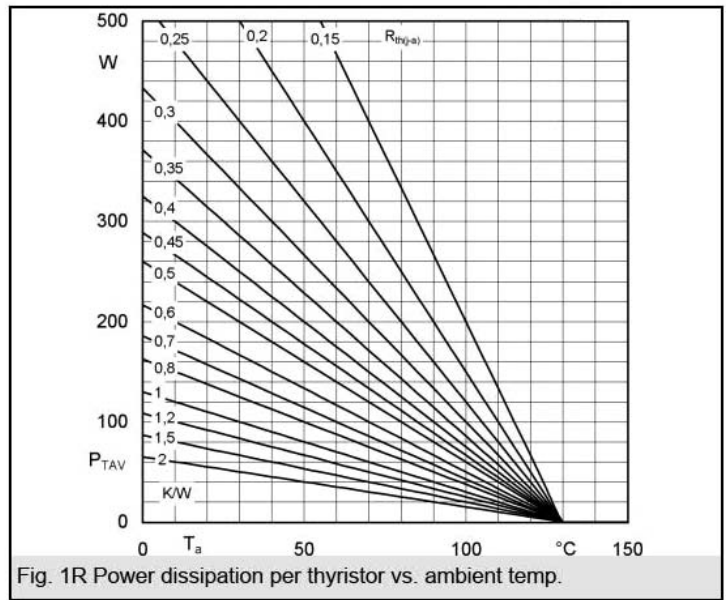
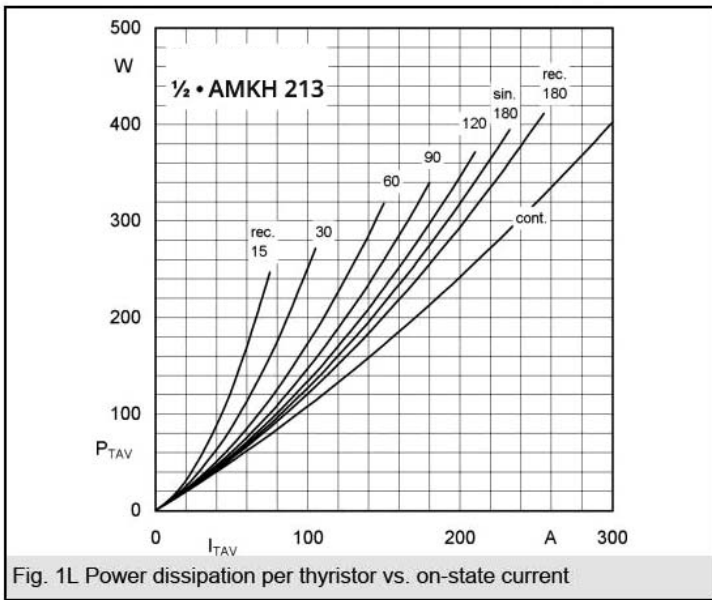
# Thyristor Diode Modules

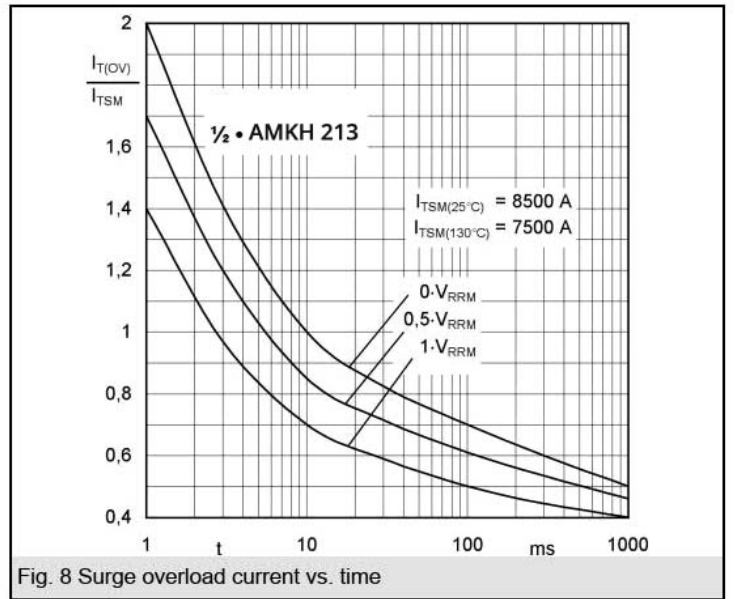
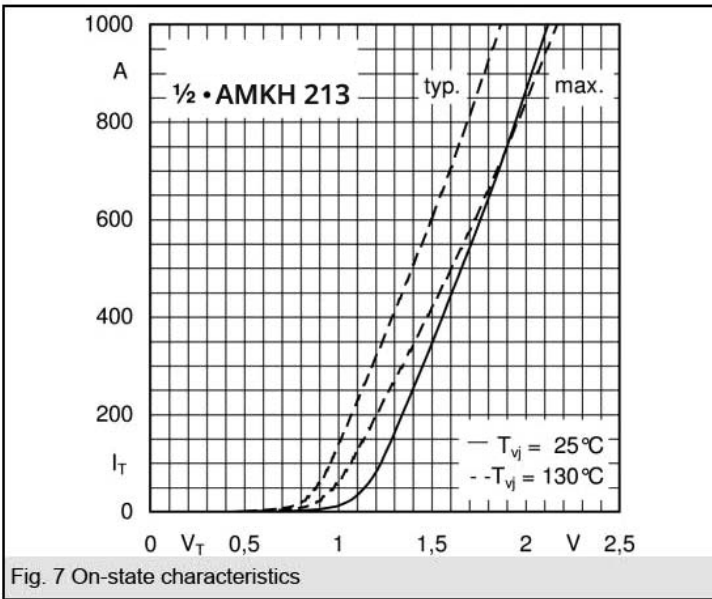
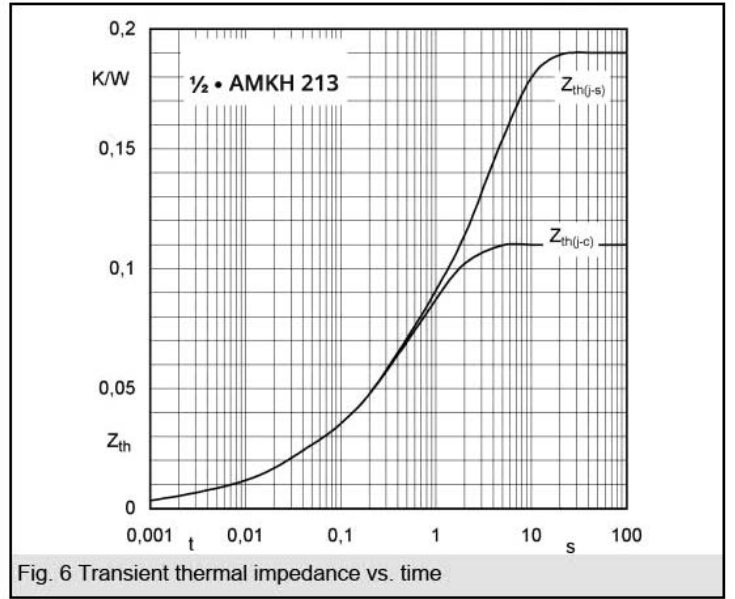
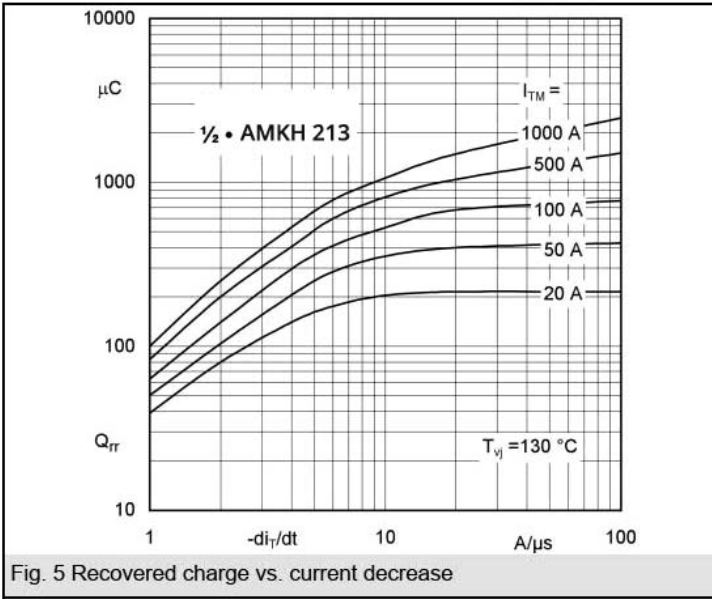
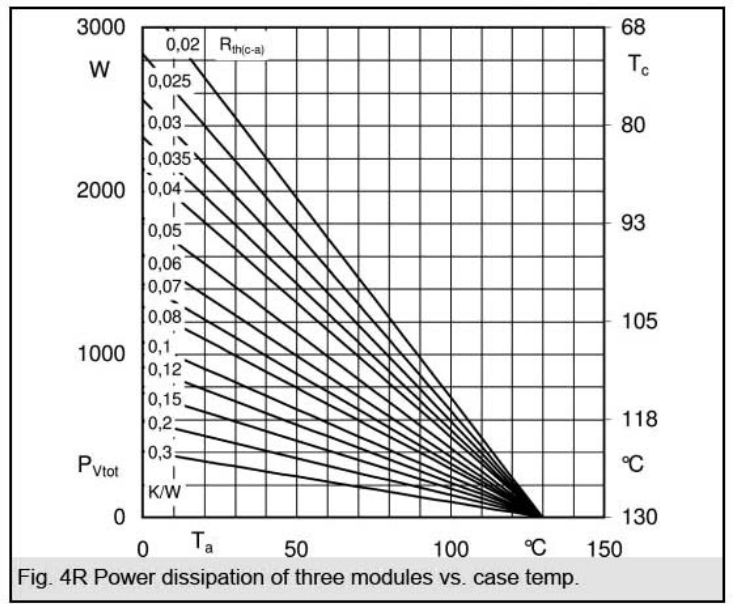
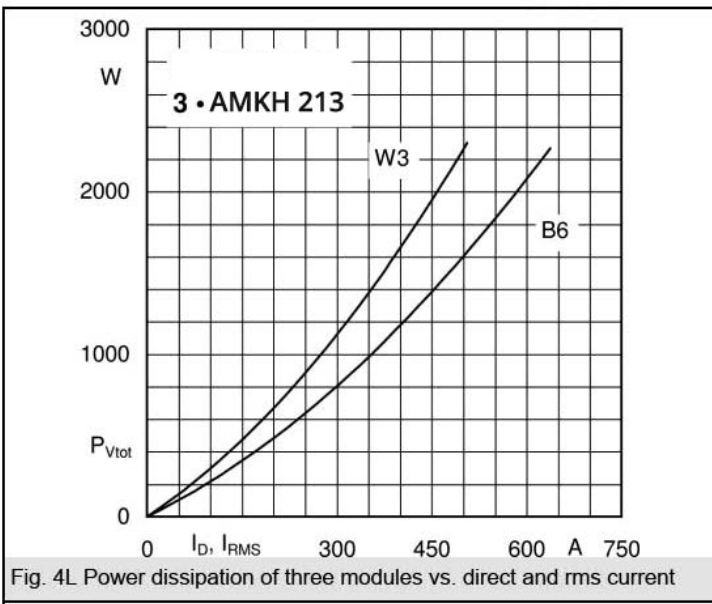
## AMKH 213

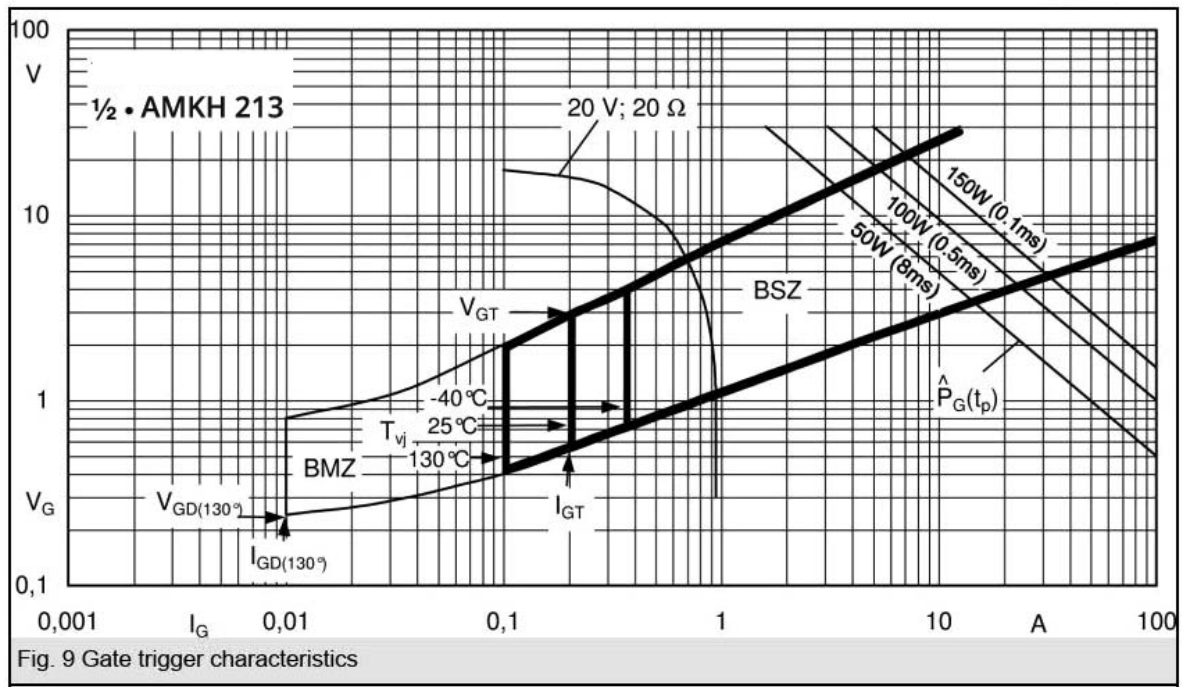


$V_{RSM}$ V	$V_{RRM}, V_{DRM}$ V	$I_{TRMS} = 370$ A (maximum value for continuous operation) $I_{TAV} = 213$ A (sin 180; $T_C = 90$ °C)	
900	800	AMKT 213-08E	–
1300	1200	AMKT 213-12E	AMKH 213-12E
1500	1400	AMKT 213-14E	AMKH 213-14E
1700	1600	AMKT 213-16E	AMKH 213-16E
1900	1800	AMKT 213-18E	AMKH 213-18E

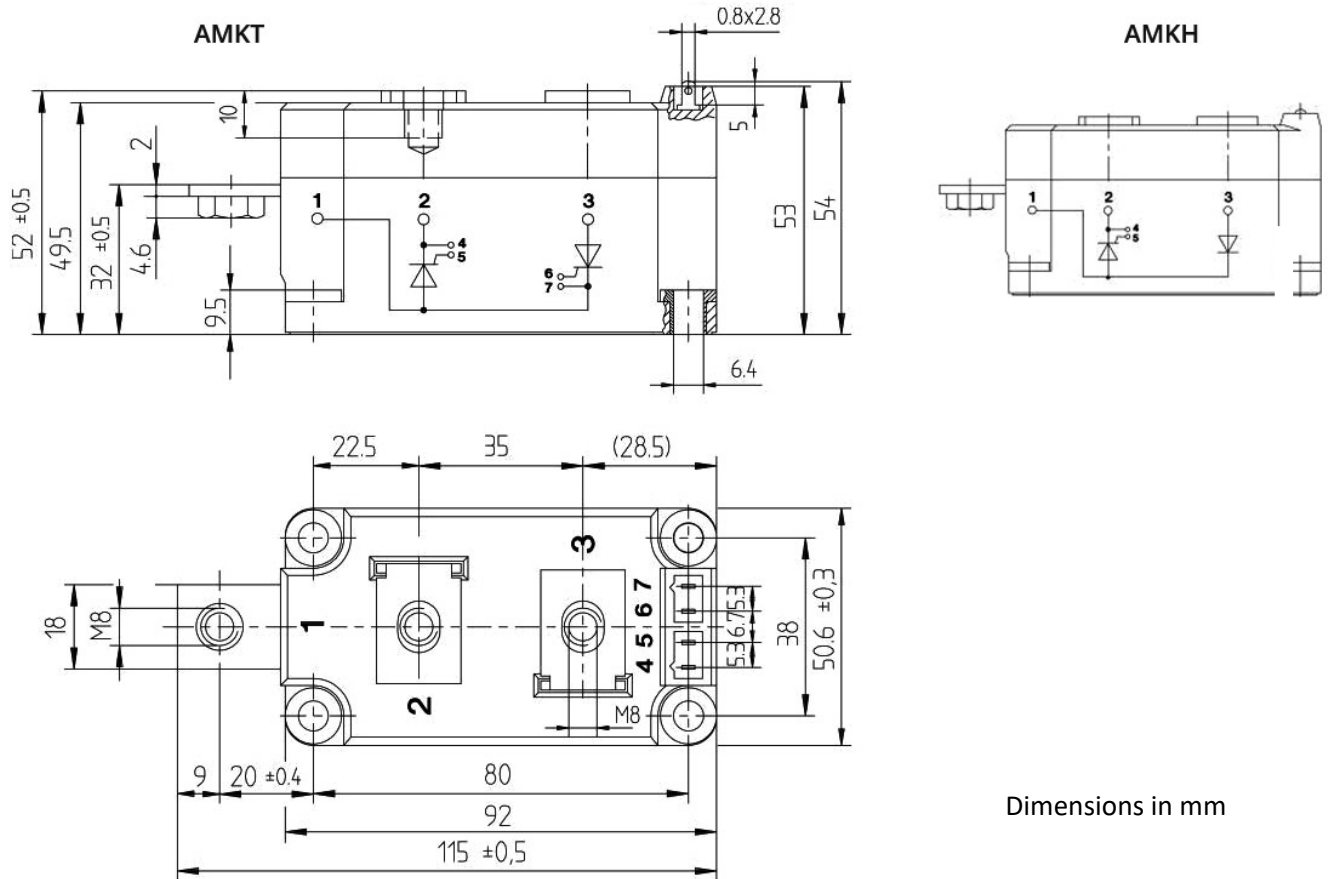
Symbo ls d r e t e r s			u e s	u n i t s
$I_{TA}$	Average on-state current	sin 180; $T_C = 85$ (100)°C	230(173)	A
$I_D$	Direct output current	P16/200F; $T_a = 35$ °C; B2/B6	354 / 456	A
$I_{RMS}$	Maximum RMS current	P16/200F; $T_a = 35$ °C; W1/W3	425 / 3*360	A
$I_{TSM}$	Surge on-state current	$T_{vj} = 25$ °C; 10 ms $T_{vj} = 130$ °C; 10 ms	8500 7500	A A
$I^2t$	$I^2t$ value, rating for fusing	$T_{vj} = 25$ °C; 8.3...10 ms $T_{vj} = 130$ °C; 8.3...10 ms	361000 281000	$A^2s$ $A^2s$
$V_T$	On-state voltage	$T_{vj} = 25$ °C; $I_T = 750$ A	max. 1.9	V
$V_{TTO}$	On-state threshold voltage	$T_{vj} = 130$ °C	0.95	V
$r_T$	On-state slope resistance	$T_{vj} = 130$ °C	1.3	mΩ
$I_{DD} I_{RD}$	Forward off-state current; Direct reverse current	$T_{vj} = 130$ °C, $V_{RD} = V_{RRM}$ ; $V_{DD} = V_{DRM}$	max. 50	mA
$t_d$	Gate controlled turn-on delay time	$T_{vj} = 25$ °C; $I_G = 1$ A; $di_G/dt = 1$ A/μs	1	μs
$t_r$	Gate controlled rise time	$V_D = 0,67 * V_{DRM}$	2	μs
$di/dt_r$	Critical rate of rise of on-state current	$T_{vj} = 130$ °C	max. 250	A/μs
$dV/dt_r$	Critical rate of rise of off-state voltage	$T_{vj} = 130$ °C	max. 500 / 1000	V/μs
$t$	Turn-off time	$T_{vj} = 130$ °C	50...150	μs
$I_H$	Holding current	$T_{vj} = 25$ °C; typ. / max	150 / 500	mA
$I_L$	Latching current	$T_{vj} = 25$ °C; $R_G = 33$ Ω; typ. / max	300 / 2000	mA
$V_{GT}$	Gate trigger voltage	$T_{vj} = 25$ °C; d.c.	min. 3	V
$I_{GT}$	Gate trigger current	$T_{vj} = 25$ °C; d.c.	min. 200	mA
$V_{GD}$	Gate non-trigger voltage	$T_{vj} = 130$ °C; d.c.	max. 0.25	V
$I_{GD}$	Gate non-trigger current	$T_{vj} = 130$ °C; d.c.	max. 10	mA
$R_{th}$	Thermal resistance, junction to case	cont.; per thyristor/per module sin.180; per thyristor / per module rec.120; per thyristor / per module	0.11 / 0.055 0.115 / 0.057 0.125 / 0.0625	K/W K/W K/W
$R_{th_s}$	Thermal resistance, junction to heatsink	per thyristor / per module	0.08 / 0.04	K/W
$T$	Virtual junction temperature		- 40 ... + 130	°C
$T_{st}$	Storage temperature range		- 40 ... + 130	°C
$V_{ISOL}$	Insulation test voltage (r.m.s.)	a.c. 50 Hz; r.m.s.; 1s / 1min.	3600 / 3000	V~
$M_s$	Mounting torque on heatsink		5 ± 15 %	Nm
$M_t$	Mounting torque for terminals		9 ± 15 %	Nm
	Maximum allowable acceleration		5 * 9.81	m/s <sup>2</sup>
	Weight	approx.	400	g







### DIMENSIONS



### TOPOLOGY OF INTERNAL CONNECTION

